

## N-CHANNEL ENHANCEMENT MODE MOSFET

**DMG1012UW** 

### Features

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Lead Free By Design/RoHS Compliant (Note 1)
- ESD Protected Up To 2KV
- "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

#### **Mechanical Data**

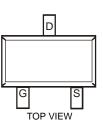
- Case: SOT-323
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Terminals: Finish Matte Tin annealed over Alloy 42
- leadframe. Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 2
- Ordering Information: See Page 2
- Weight: 0.006 grams (approximate)





Gate Protection Diode EQUIVALENT CIRCUIT

Drain



### **Maximum Ratings** $@T_A = 25^{\circ}C$ unless otherwise specified

Char	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DSS</sub>	20	V
Gate-Source Voltage	V <sub>GSS</sub>	±6	V
Continuous Drain Current (Note 3)	ID	1.0 0.64	А
Pulsed Drain Current (Note 4)	I <sub>DM</sub>	6	А

## **Thermal Characteristics**

Characteristic	Symbol	Max	Unit
Power Dissipation (Note 3)	PD	0.29	W
Thermal Resistance, Junction to Ambient $@T_A = 25^{\circ}C$ (Note 3)	R <sub>0JA</sub>	425	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

Notes: 1. No purposefully added lead.

2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead\_free/index.php.

3. Device mounted on FR-4 PCB, with minimum recommended pad layout.

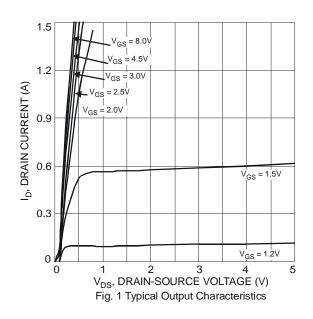
4. Repetitive rating, pulse width limited by junction temperature.

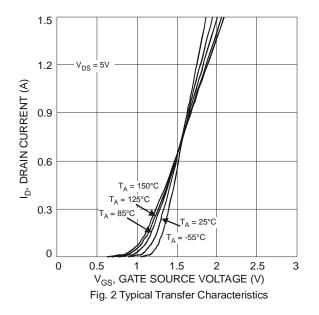


## **Electrical Characteristics** $@T_A = 25^{\circ}C$ unless otherwise specified

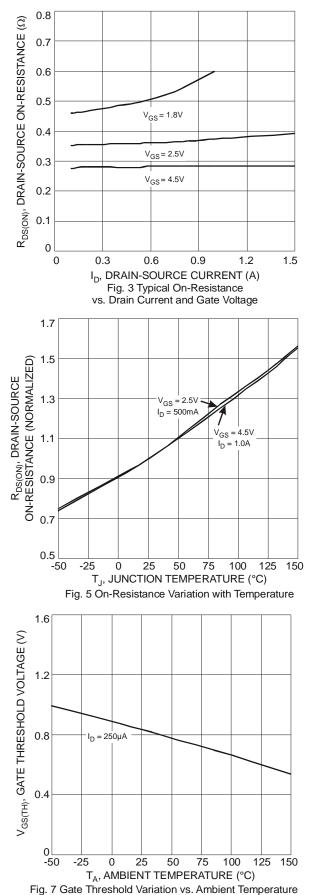
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 5)						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	20	-	-	V	$V_{GS} = 0V, I_D = 250 \mu A$
Zero Gate Voltage Drain Current T <sub>J</sub> = 25°C	I <sub>DSS</sub>	-	-	100	nA	$V_{DS} = 20V, V_{GS} = 0V$
Gate-Source Leakage	I <sub>GSS</sub>	-	-	±1.0	μA	$V_{GS} = \pm 4.5 V, V_{DS} = 0 V$
ON CHARACTERISTICS (Note 5)						
Gate Threshold Voltage	V <sub>GS(th)</sub>	0.5	-	1.0	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$
			0.3	0.45		$V_{GS} = 4.5V, I_D = 600mA$
Static Drain-Source On-Resistance	R <sub>DS (ON)</sub>	-	0.4	0.6	Ω	$V_{GS} = 2.5V, I_D = 500mA$
			0.5	0.75		$V_{GS} = 1.8V, I_D = 350mA$
Forward Transfer Admittance	Y <sub>fs</sub>	-	1.4	-	S	$V_{DS} = 10V, I_D = 400mA$
Diode Forward Voltage	V <sub>SD</sub>		0.7	1.2	V	$V_{GS} = 0V, I_{S} = 150mA$
DYNAMIC CHARACTERISTICS (Note 6)						
Input Capacitance	C <sub>iss</sub>	-	60.67	-	pF	
Output Capacitance	Coss	-	9.68	-	pF	V <sub>DS</sub> = 16V, V <sub>GS</sub> = 0V, f = 1.0MHz
Reverse Transfer Capacitance	C <sub>rss</sub>	-	5.37	-	pF	
Total Gate Charge	Qg	-	736.6	-	рС	
Gate-Source Charge	Q <sub>gs</sub>	-	93.6	-	рС	$V_{GS} = 4.5V, V_{DS} = 10V,$
Gate-Drain Charge	Q <sub>gd</sub>	-	116.6	-	рС	– I <sub>D</sub> = 250mA
Turn-On Delay Time	t <sub>D(on)</sub>	-	5.1	-	ns	
Turn-On Rise Time	tr	-	7.4	-	ns	$V_{DD} = 10V, V_{GS} = 4.5V,$
Turn-Off Delay Time	t <sub>D(off)</sub>	-	26.7	-	ns	$R_{L} = 47\Omega, R_{G} = 10\Omega,$
Turn-Off Fall Time	tf	-	12.3	-	ns	$-I_D = 200 \text{mA}$

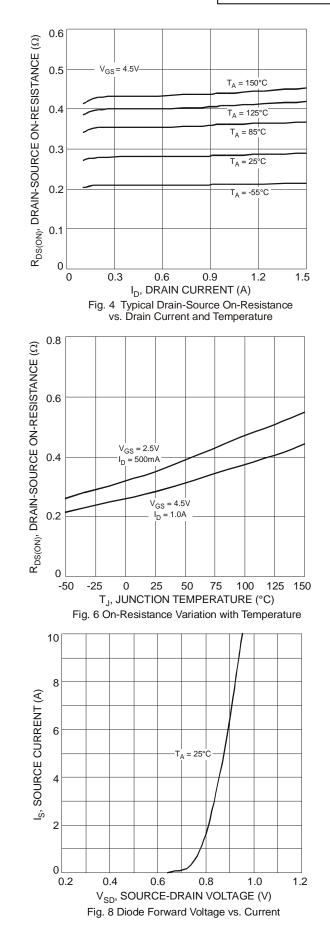
Notes: 5. Short duration pulse test used to minimize self-heating effect. 6. Guaranteed by design. Not subject to production testing.







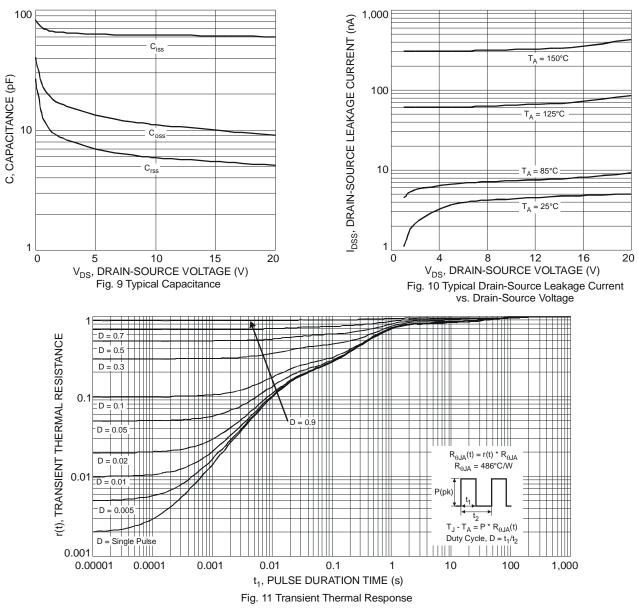




DMG1012UW Document number: DS31859 Rev. 3 - 2



## **DMG1012UW**



#### Ordering Information (Note 7)

Part Number	Case	Packaging
DMG1012UW-7	SOT-323	3000 / Tape & Reel

Notes: 7. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

## **Marking Information**



NA1 = Product Type Marking Code YM = Date Code Marking

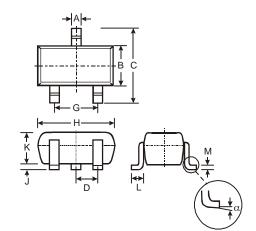
Y = Year (ex: W = 2009)

M = Month (ex: 9 = September)

Date Cod	le Key												
Ye	ear	200	9	2010		2011	20	12	2013		2014	2	2015
Co	ode	W		Х		Y		Ζ	А		В		С
Мо	onth	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Co	ode	1	2	3	4	5	6	7	8	9	0	N	D

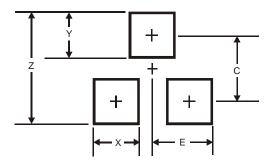


# Package Outline Dimensions



SOT-323						
Dim	Min	Max	Тур			
Α	0.25	0.40	0.30			
В	1.15	1.35	1.30			
С	2.00	2.20	2.10			
D	-	-	0.65			
G	1.20	1.40	1.30			
н	1.80	2.20	2.15			
J	0.0	0.10	0.05			
κ	0.90	1.00	1.00			
L	0.25	0.40	0.30			
М	0.10	0.18	0.11			
α	0°	8°	-			
All Dimensions in mm						

# Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.8
Х	0.7
Y	0.9
С	1.9
E	1.0

NEW PRODUCT



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